IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

1 (Currently Amended). [[An]] A p-type electrode material represented by a composition formula $A_XB_YC_Z$, characterized in that:

A consists of at least one element selected from Group 1B metal elements,

B consists of at least one element selected from Group 8 metal elements, and

C consists of at least one element selected from S and Se,

wherein mole ratios X, Y, and Z are such that $X+Y+Z=1$, $0.20 \leq X \leq 0.35$, $0.17 \leq Y \leq 0.30$, and $0.45 \leq Z \leq 0.55$.

2 (Currently Amended). [[An]] A p-type electrode material according to claim 1, characterized in that said A comprises Cu, and said B comprises Fe.

3 (Currently Amended). [[An]] A p-type electrode material according to claim 1 or 2, characterized in that said p-type electrode material has a chalcopyrite structure.

4 (Currently Amended). A p-type semiconductor element characterized by having a structure wherein a Group II-VI compound semiconductor and the p-type electrode material according to ~~any of claims 1 to 3~~ claim 1 are in contact with each other.

5 (Currently Amended). A p-type semiconductor element characterized by comprising a semiconductor having a Group II-VI compound semiconductor layer at at least an

outermost surface layer, and

the p-type electrode material according to ~~any of claims 1 to 3~~ claim 1 which is in contact with said semiconductor via said Group II-VI compound semiconductor layer.

6 (Currently Amended). A p-type semiconductor element characterized by comprising

a semiconductor having a Group II-VI compound semiconductor layer at at least an outermost surface layer, and

a hole-injection electrode portion placed in contact with said semiconductor via said Group II-VI compound semiconductor layer and made of a solid solution material of a compound $A_XB_YC_Z$ in the form of the p-type electrode material according to ~~any of claims 1 to 3~~ claim 1 and a Group II-VI compound semiconductor.

7 (Currently Amended). A p-type semiconductor element according to claim 6, characterized in that components of said compound $A_XB_YC_Z$ in said hole-injection electrode portion decrease continuously or stepwise from the surface toward said Group II-VI compound semiconductor layer.

8 (Currently Amended). A p-type semiconductor element according to ~~any of claims 4 to 7~~ claim 4, characterized in that the Group II-VI compound semiconductor contains at least Zn as a Group II element and at least one element selected from S and Se as a Group VI element.

9 (Currently Amended). A p-type semiconductor element characterized by having a structure wherein a Group III-V compound semiconductor and the electrode material according to

~~any of claims 1 to 3~~ claim 1 are in contact with each other.

10 (Currently Amended). A p-type semiconductor element characterized by having a structure wherein an organic semiconductor and the p-type electrode material according to ~~any of claims 1 to 3~~ claim 1 are in contact with each other.

11 (Currently Amended). A p-type semiconductor element according to any of claims 4 to 10, characterized in that said p-type semiconductor element is a semiconductor light-emitting element.